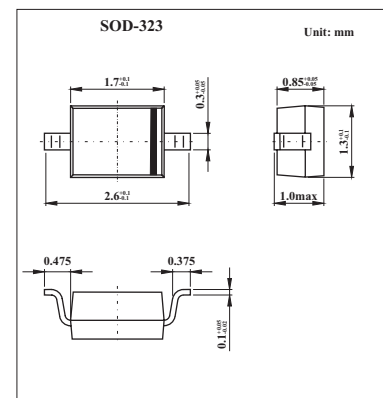


Silicon PIN Diode

BAR64-03W

■ Features

- High voltage current controlled RF resistor for RF attenuator and switches
- Frequency range above 1 MHz
- Low resistance and short carrier lifetime
- For frequencies up to 3 GHz



■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Value	Unit
Reverse voltage	V _R	200	V
Forward current	I _F	100	mA
Total Power dissipation Ts ≤ 25 °C	P _{tot}	250	mW
Junction temperature	T _j	150	°C
Operating temperature range	T _{op}	-55 to +150 °C	°C
Storage temperature range	T _{stg}	-55 to +150 °C	°C
Junction - soldering point ¹⁾	R _{thJA}	≤ 450	K/W

Note:

1.Package mounted on alumina 15mm x 16.7mm x 0.7mm

■ Electrical Characteristics Ta = 25 °C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakdown voltage	V _(BR)	I _R = 5 μA	200			V
Forward voltage	V _F	V _R = 20 V, f = 1 MHz			1.1	V
Diode capacitance	C _T	V _R = 0 V, f = 100 MHz		0.23	0.35	pF
Forward resistance	r _f	I _F = 1 mA, f = 100 MHz		12.5	20	Ω
		I _F = 10 mA, f = 100 MHz		2.1	3.8	
		I _F = 100 mA, f = 100 MHz		0.85	1.35	
Charge carrier life time	τ _{rr}	I _F = 10 mA, I _R = 6 mA, I _R = 3mA		1.55		μs
Series inductance	L _s			2		nH

■ Marking

Marking	2
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